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# SOT-323

## 2SC5876W

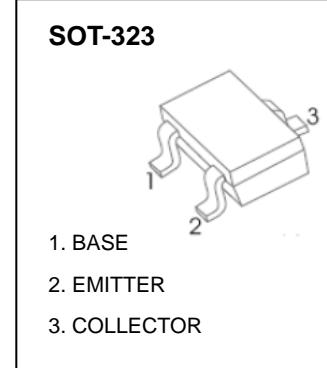


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### 2SC5876W TRANSISTOR (NPN)

#### ● Features

- 1) High speed switching.  
( $T_f$ : Typ.: 80ns at  $I_C = 500mA$ )
- 2) Low saturation voltage, typically  
(Typ.: 150mV at  $I_C = 100mA, I_B = 10mA$ )
- 3) Strong discharge power for inductive load and capacitance load.
- 4) Complements the 2SA2088W.



#### ● Application

LOW FREQUENCY AMPLIFIER, HIGH SPEED SWITCHING

#### ● Marking: VS

#### ● Absolute maximum ratings ( $T_a = 25^\circ C$ )

Parameter	Symbol	Values	Unit
Collector-base voltage	$V_{CBO}$	60	V
Collector-emitter voltage	$V_{CEO}$	60	V
Emitter-base voltage	$V_{EBO}$	6	V
Collector current	$I_C$	500	mA
	$I_{CP}^{*1}$	1.0	A
Power dissipation	$P_D^{*2}$	200	mW
Junction temperature	$T_j$	150	°C
Range of storage temperature	$T_{stg}$	-55 to + 150	°C



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### ● Electrical characteristics ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Collector-base breakdown voltage	$\text{BV}_{\text{CBO}}$	$I_C = 100 \mu\text{A}$	60	-	-	V
Collector-emitter breakdown voltage	$\text{BV}_{\text{CEO}}$	$I_C = 1 \text{ mA}$	60	-	-	V
Emitter-base breakdown voltage	$\text{BV}_{\text{EBO}}$	$I_E = 100 \mu\text{A}$	6	-	-	V
Collector cut-off current	$I_{\text{CBO}}$	$V_{\text{CB}} = 40 \text{ V}$	-	-	1	$\mu\text{A}$
Emitter cut-off current	$I_{\text{EBO}}$	$V_{\text{EB}} = 4 \text{ V}$	-	-	1	$\mu\text{A}$
Collector-emitter saturation voltage	$V_{\text{CE}(\text{sat})}$	$I_C = 100 \text{ mA}, I_B = 10 \text{ mA}$	-	150	300	mV
DC current gain	$h_{\text{FE}}$	$V_{\text{CE}} = 2 \text{ V}, I_C = 50 \text{ mA}$	120	-	390	-
Transition frequency	$f_T^{*3}$	$V_{\text{CE}} = 10 \text{ V}, I_E = -100 \text{ mA}, f = 100 \text{ MHz}$	-	300	-	MHz
Output capacitance	$C_{\text{ob}}$	$V_{\text{CB}} = 10 \text{ V}, I_E = 0 \text{ mA}, f = 1 \text{ MHz}$	-	5	-	pF
Turn-On time	$t_{\text{on}}^{*3}$	$I_C = 500 \text{ mA}, I_{B1} = 50 \text{ mA}, I_{B2} = -50 \text{ mA}, V_{\text{CC}} \approx 25 \text{ V}, R_L = 50 \Omega$ See test circuit	-	70	-	ns
Storage time	$t_{\text{stg}}^{*3}$	$I_C = 500 \text{ mA}, I_{B1} = 50 \text{ mA}, I_{B2} = -50 \text{ mA}, V_{\text{CC}} \approx 25 \text{ V}, R_L = 50 \Omega$ See test circuit	-	130	-	ns
Fall time	$t_f^{*3}$		-	80	-	ns

\*1  $P_w=10\text{ms}$

\*2 Each terminal mounted on a reference land.

\*3 Pulsed



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### Typical Characteristics

Fig.1 Ground Emitter Propagation Characteristics

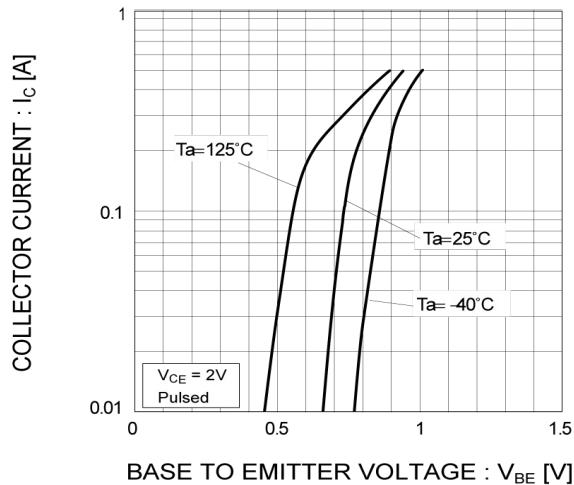


Fig.2 Typical Output Characteristics

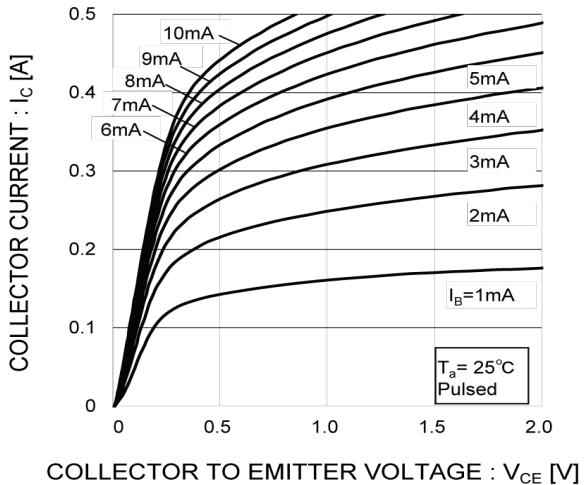


Fig.3 DC Current Gain vs. Collector Current (I)

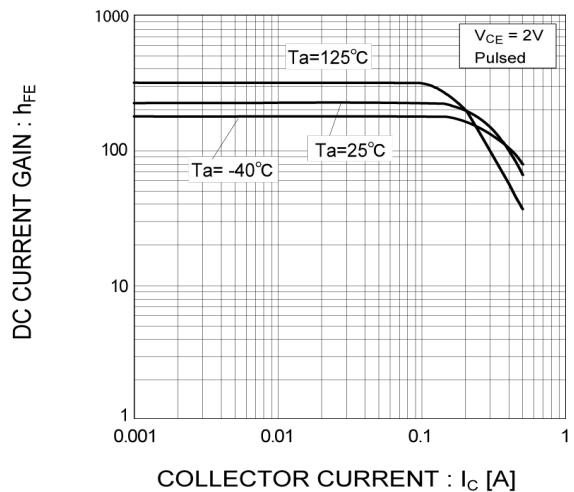


Fig.4 DC Current Gain vs. Collector Current (II)

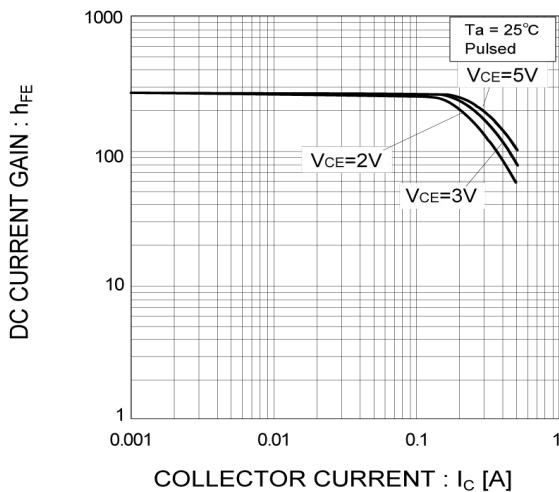


Fig.5 Collector-Emitter Saturation Voltage vs. Collector Current (I)

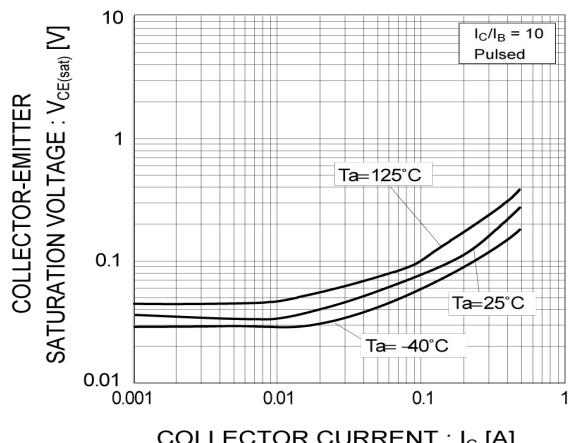
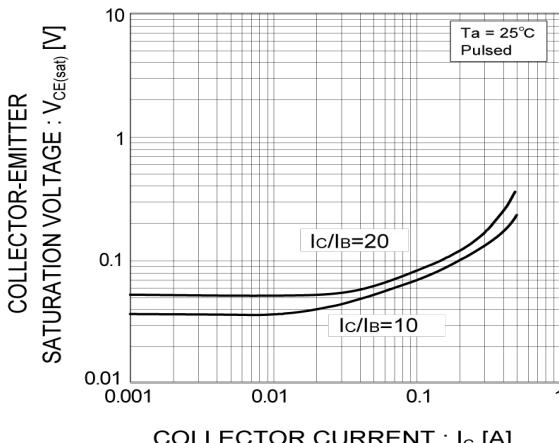


Fig.6 Collector-Emitter Saturation Voltage vs. Collector Current (II)





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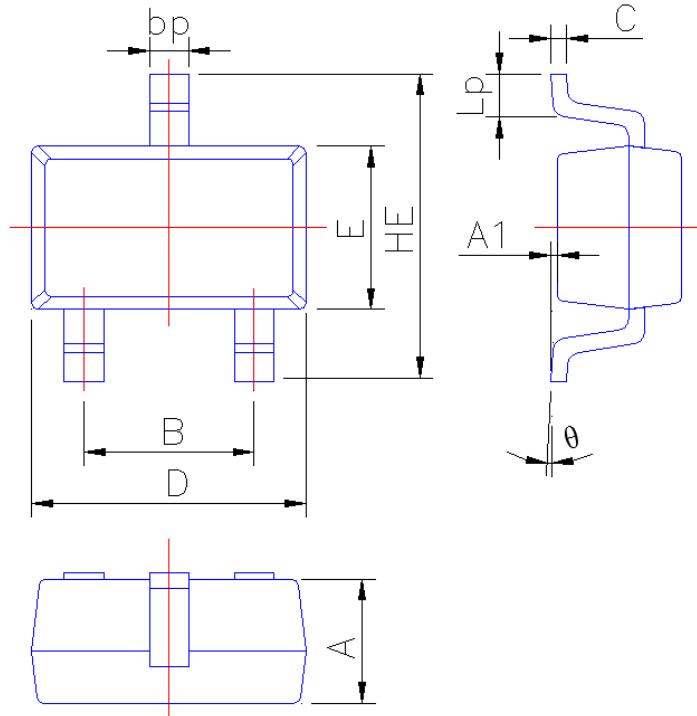


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## PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-323



Symbol	Dimension in Millimeters	
	Min	Max
A	0.90	1.00
A1	0.010	0.100
B	1.20	1.40
bp	0.25	0.45
C	0.09	0.15
D	2.00	2.20
E	1.15	1.35
HE	2.15	2.55
Lp	0.25	0.46
θ	0°	6°